# **BGA715L7**

Silicon Germanium GPS Low Noise Amplifier

**Small Signal Discretes** 



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BGA715	L7						
Revisio	n History: 2009-10-9, Rev.2.1						
Previou	s Version: 2008-09-12, Rev.2.0						
Page	e Subjects (major changes since last revision)						
5	Ambient temperature range is extended down to -40°C						



Silicon Germanium GPS Low Noise Amplifier

### 1 Silicon Germanium GPS Low Noise Amplifier

#### **Features**

High gain: 20 dB

Low Noise Figure: 0.7 dB

• Low current consumption: 3.3 mA

Supply voltage: 1.5 V to 3.3 V

High input compression point -15.5 dBm at 1.8 V supply

High input 3rd intercept point -7 dBm at 1.8 V supply

B7HFM Silicon Germanium technology

• RF output internally matched to 50  $\Omega$ 

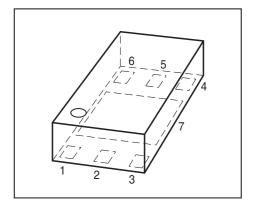
· Low external part count

2kV HBM ESD protection (including Al-pin)

Tiny TSLP-7-1 leadless package

· Moisture sensitivity level: MSL 1

Pb-free (RoHS compliant) package



**TSLP-7-1** 



#### **Application**

· 1575 MHz GPS, Galileo, GPS phone

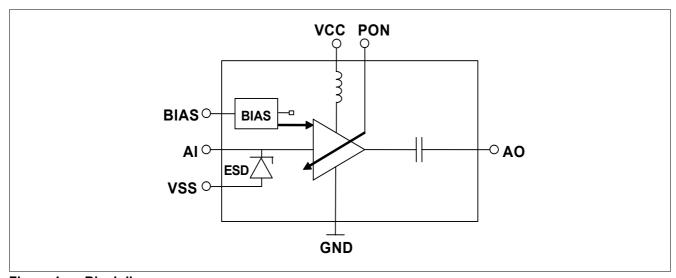


Figure 1 Blockdiagram

## 2 Description

The BGA715L7 is a front-end low noise amplifier for Global Positioning System (GPS) applications. The LNA provides 20 dB gain, 0.7 dB noise figure and high linearity performance in the application configuration described in **Chapter 4**. Current consumption is as low as 3.3 mA. The BGA715L7 is based upon Infineon Technologies' B7HFM Silicon Germanium technology. It operates over a 1.5 V to 3.3 V supply range.

If an ultra low noise figure of 0.6 dB is required, please refer to Infineon BGA715L7 Application Note AN161.



**Description** 

Туре	Package	Marking
BGA715L7	TSLP-7-1	UG

#### **Pin Definition and Function**

#### Table 1 Pin Definition and Function

Pin No.	Symbol	Function
1	Al	LNA input
2	BIAS	DC bias
3	GND	RF ground
4	PON	Power on control
5	VCC	DC supply
6	AO	LNA output
7	VSS	DC ground

#### **Maximum Ratings**

Table 2 Maximum Ratings

Parameter <sup>1)</sup>	Symbol	Value	Unit
Voltage at pin VCC	$V_{CC}$	-0.3 3.6	V
Voltage at pin Al	$V_{Al}$	-0.3 0.9	V
Voltage at pin BIAS	$V_{BIAS}$	-0.3 0.9	V
Voltage at pin AO	$V_{AO}$	-0.3 V <sub>CC</sub> + 0.3	V
Voltage at pin PON	$V_{PON}$	-0.3 V <sub>CC</sub> + 0.3	V
Voltage at pin GND	$V_{GND}$	-0.3 0.3	V
Current into pin VCC	$I_{\rm CC}$	10	mA
RF input power	$P_{IN}$	10	dBm
Total power dissipation	$P_{tot}$	36	mW
Junction temperature	$T_{J}$	150	°C
Ambient temperature range	$T_{A}$	-40 85	°C
Storage temperature range	$T_{STG}$	-65 150	°C
<sup>2)</sup> Human Body Model ESD capability, all pin to all pin	$V_{\mathrm{ESD\_HBM}}$	2000	V
3)Machine Model ESD capability, all pin to all pin	$V_{ESD\_MM}$	100	V

<sup>1)</sup> All voltages refer to VSS-Node.

#### Thermal resistance

Table 3 Thermal resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	159	K/W

<sup>1)</sup> For calculation of  $R_{\mathrm{thJA}}$  please refer to Application Note Thermal Resistance

<sup>2)</sup> According to JEDS22A-114

<sup>3)</sup> According to JEDS22A-115



**Electrical Characteristics** 

### 3 Electrical Characteristics

Table 4 Electrical Characteristics<sup>1)</sup>:  $T_{\rm A}$  = 25 °C,  $V_{\rm CC}$  = 1.8 V,  $V_{\rm PON,ON}$  = 1.8 V,  $V_{\rm PON,OFF}$  = 0 V, f = 1575 MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Тур.	Max.		
Supply voltage	$V_{CC}$	1.5	1.8	3.6	V	
Supply current	$I_{CC}$	-	3.3	-	mA	ON-mode
		-	0.2	3	μΑ	OFF-mode
Gain switch control voltage	$V_{pon}$	1.0	-	Vcc	V	ON-mode
		0	-	0.4	V	OFF-mode
Gain switch control current	$I_{pon}$	-	5		μΑ	ON-mode
		-		1	μΑ	OFF-mode
Power gain	$ S_{21} ^2$	-	20	-	dB	High-gain Mode
Noise figure <sup>2)</sup>	NF	-	0.7	-	dB	$Z_{\rm S}$ = 50 $\Omega$
Input return loss	$RL_{in}$	-	14	-	dB	
Output return loss	$RL_{out}$	-	13	-	dB	
Reverse isolation	$1/ S_{12} ^2$	-	43	-	dB	
Power gain settling time <sup>3)</sup>	$t_{S}$	-	5	-	μs	OFF- to ON-mode
		-	5	-	μs	ON- to OFF-mode
Inband input 1dB compression point	IP <sub>1dB</sub>	-	-15.5	-	dBm	
Inband input 3rd order intercept point <sup>4)</sup>	$IIP_3$	-	-7	-	dBm	$f_1 = 1575 \text{ MHz}$ $f_2 = f_1 + /-1 \text{ MHz}$
Stability	k	-	> 1	-		f = 20 MHz 20 GHz

<sup>1)</sup> Measured on BGA715L7 application board according to application schematic on page 7, including PCB losses (unless noted otherwise)

<sup>2)</sup> PCB tranmission line- and connector losses of 0.05dB are subtracted

<sup>3)</sup> To be within 1 dB of the final gain OFF- to ON-mode; to be within 3 dB of the final gain ON- to OFF-mode

<sup>4)</sup> Input Power = -30 dBm for each tone



**Application Information** 

## 4 Application Information

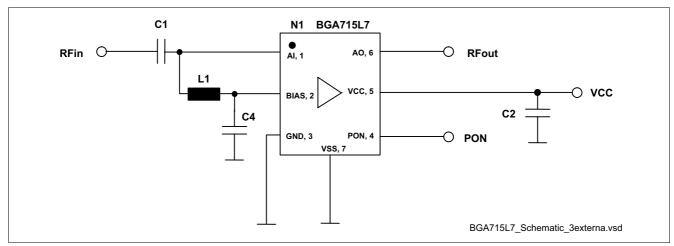


Figure 2 Application Schematic BGA715L7

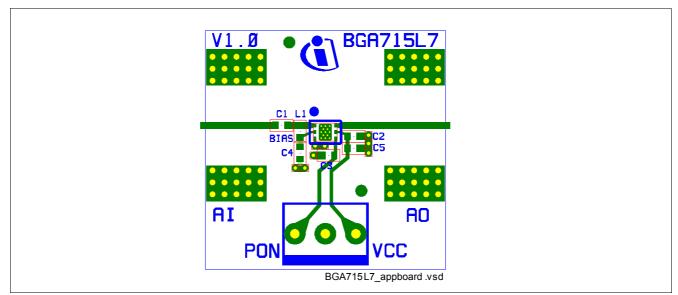


Figure 3 Application Board Drawing BGA715L7

Table 5 Bill of Materials

Name	Value	Package	Manufacturer	Function
C1	1.8 pF	0402	Various	DC blocking and input matching
C2	1 μF	0402	Various	RF block
C4	15 pF	0402	Various	RF block
L1	4.7 nH LQW15A series	0402	Murata	Bias feed and input matching
N1	BGA715L7	TSLP-7-1	Infineon	SiGe LNA

A list of all application notes is available at <a href="http://goto.infineon.com/smallsignaldiscretes-appnotes">http://goto.infineon.com/smallsignaldiscretes-appnotes</a>.



**Package Information** 

## 5 Package Information

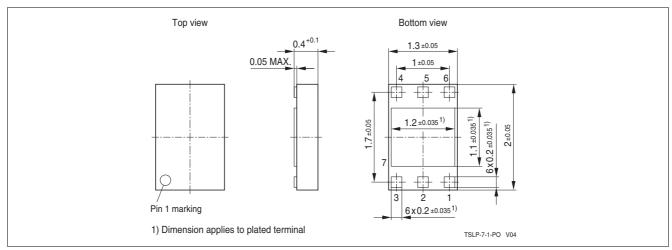


Figure 4 Package Dimensions for TSLP-7-1

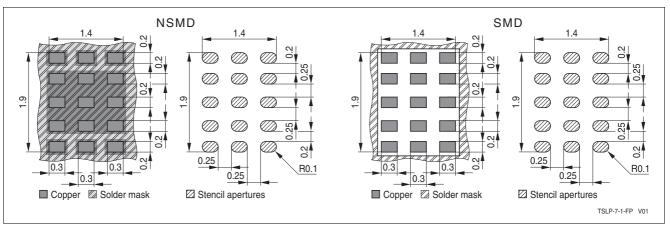


Figure 5 Footprint TSLP-7-1

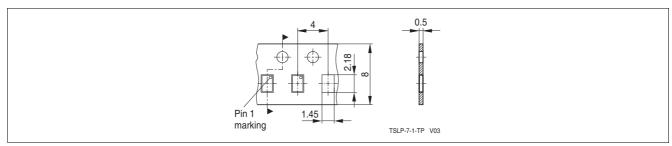


Figure 6 Tape & Reel Dimensions (Ø reel 180, pieces/reel 7500)